

L Number	Hits	Search Text	DB	Time stamp
1	509	((second near (semiconductor near2 (layer or film))) same (barrier near2 (layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/09 14:28
2	17852	getter or gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/09 14:28
3	49	((second near (semiconductor near2 (layer or film))) same (barrier near2 (layer or film))) and (getter or gettering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/09 14:28
4	2598	semiconductor adj energy adj laboratory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/09 14:29
5	2566	(semiconductor adj energy adj laboratory) not (((second near (semiconductor near2 (layer or film))) same (barrier near2 (layer or film))) and (getter or gettering))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/09 14:29
6	17	((second near (semiconductor near2 (layer or film))) same (barrier near2 (layer or film))) and (getter or gettering) not (semiconductor adj energy adj laboratory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/09 14:29
-	7530	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/09 14:25
-	202151	inert near2 gas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 17:58
-	5995238	semiconductor near\$2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:10
-	389182	(metallic or metal) near2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:55
-	111146	(inert near2 gas) and (semiconductor near\$2 (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:56
-	18453	((inert near2 gas) and (semiconductor near\$2 (layer or film))) and ((metallic or metal) near2 (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:56
-	381	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((inert near2 gas) and (semiconductor near\$2 (layer or film))) and ((metallic or metal) near2 (layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 19:04

-	17841	getter or gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/09 14:28
-	56	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((inert near2 gas) and (semiconductor near\$2 (layer or film))) and ((metallic or metal) near2 (layer or film)))) and (getter or gettering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 19:05